L Number	Hits	Search Text	DB	Time stamp
1	2	5824599.pn. 6020266.pn.	USPAT;	2004/03/04 15:39
			US-PGPUB	
2	3585	257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls.	USPAT;	2004/03/04 16:33
		257/768.ccls. 257/769.ccls. 257/774.ccls.	US-PGPUB	
3	0	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls.	USPAT;	2004/03/04 17:18
		257/768.ccls. 257/769.ccls. 257/774.ccls.) and ((gate with	US-PGPUB	
		(platinum pt rhodium rh ruthenium ru iridium ir osmium os))		
		same ((plug interconnect wiring trace via contact) with	'	
	110	(copper cu)) same (source drain)) (257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls.	USPAT;	2004/03/04 16:39
4	118	257/768.ccls. 257/769.ccls. 257/764.ccls.) and (gate with	US-PGPUB	2004/03/04 10.39
		(platinum pt rhodium rh ruthenium ru iridium ir osmium os))	03-70700	
5	14	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls.	USPAT;	2004/03/04 16:39
		257/768.ccls. 257/769.ccls. 257/774.ccls.) and (polysilicon	US-PGPUB	200 1,00,0 1 20.03
		with gate with (platinum pt rhodium rh ruthenium ru iridium	00.00	
		ir osmium os))		
6	15	((gate with (platinum pt rhodium rh ruthenium ru iridium ir	USPAT;	2004/03/04 16:55
		osmium os)) same ((plug interconnect wiring trace via	US-PGPUB	
		contact) with (copper cu)) same (source drain))		
7	35	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls.	USPAT;	2004/03/04 17:28
		257/768.ccls. 257/769.ccls. 257/774.ccls.) and (gate same	US-PGPUB	
		((plug interconnect wiring trace via contact) with (copper		
	200	cu)) same (source drain))	USPAT;	2004/03/04 17:29
8	380	(gate same ((plug contact) with (copper cu)) same (source drain))	US-PGPUB	2004/03/04 17.29
9	13	(gate with ((plug contact) near2 (copper cu)) with (source	USPAT;	2004/03/04 17:34
•	13	(gate with ((plug contact) flear2 (copper cu/) with (source   drain))	US-PGPUB	2001/05/01 17.51
10	26	438/620.ccls. and ((plug contact) with (copper cu))	USPAT;	2004/03/04 17:36
10		(copper day)	US-PGPUB	200 1,00,01 21 100
11	547	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls.	USPAT;	2004/03/04 18:05
		257/768.ccls. 257/769.ccls. 257/774.ccls.) and ((copper cu	US-PGPUB	
		silver ag gold au platinum pt) same ((rhodium rh ruthenium		
		ru iridium ir osmium os platinum pt) with (palladium pd		
		cobalt co nickel ni titanium ti)))		
12	1	((insulat\$4 dielectric oxide dioxide nitride interlayer) with	EPO; JPO;	2004/03/04 18:06
		(silicon si)) and ((unit adj cell) (lattice near4 (constant	DERWENT;	
		mismatch\$4 match\$4))) and ((atom\$2 near (radius radii))	IBM_TDB	
13	27	(bond\$4 near energy)) ((atom\$2 near (radius radii)) (bond\$4 near energy)) and	EPO; JPO;	2004/03/04 18:06
13	21	((acomise flear (facility facility)) and (semiconductor silicon si wafer substrate) and (copper cu)	DERWENT;	200 1/05/04 10:00
		and (rhodium rh ruthenium ru iridium ir osmium os platinum	IBM_TDB	
		pt)		
14	7	(semiconductor silicon si wafer substrate) and	USPAT;	2004/03/04 18:08
		((interconnect\$5 metal\$1is\$7 metal\$1iz\$7) same ((platinum	US-PGPUB	
<u> </u>		pt) near4 (film layer multilayer bilayer trilayer "bi-layer"		
Į.		"tri-layer" "multi-layer")) same ((osmium os) with (palladium		
		pd cobalt co nickel ni titanium ti) with (film layer multilayer		
1.	244	bilayer trilayer "bi-layer" "tri-layer" "multi-layer")))	LICDAT:	2004/03/04 19:11
15	241	((atom\$2 near (radius radii)) (bond\$4 near energy)) and	USPAT; US-PGPUB	2004/03/04 18:11
		(semiconductor silicon si wafer substrate) and ((copper cu) same (rhodium rh ruthenium ru iridium ir osmium os	03-10100	
		platinum pt) same (film layer multilayer bilayer trilayer	1	
		bi-layer "tri-layer" "multi-layer"))	1	
17	199	(semiconductor silicon si wafer substrate) and ((insulat\$4	USPAT;	2004/03/04 18:11
		dielectric oxide dioxide nitride interlayer) with (silicon si))	US-PGPUB	
		and ((unit adj cell) (lattice near4 (constant mismatch\$4	1	
		match\$4))) and ((atom\$2 near (radius radii)) (bond\$4 near	1	!
		energy))		

18	365	(semiconductor silicon si wafer substrate) and ((interconnect\$5 metal\$1is\$7 metal\$1iz\$7) same ((copper cu silver ag gold au) near4 (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")) same ((rhodium rh ruthenium ru iridium ir osmium os platinum pt) with (palladium pd cobalt co nickel ni titanium ti) with (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer") with (element constituent consist\$3 compris\$3 atom	USPAT; US-PGPUB	2004/03/04 18:11
16	135	metal)))	EPO; JPO; DERWENT; IBM_TDB	2004/03/04 18:20